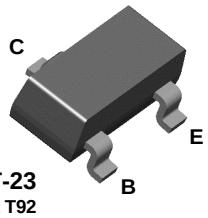
FAIRCHILD
SEMICONDUCTOR TM

BSR18A



SOT-23
Mark: T92

PNP General Purpose Amplifier

This device is designed as a general purpose amplifier and switching applications at collector currents of 10 μA to 100 mA. Sourced from Process 66.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	200	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BSR18A	
P_D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

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PNP General Purpose Amplifier
(continued)

Electrical Characteristics
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C = 10 μA, I_B = 0	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 1.0 mA, I_E = 0	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 10 μA, I_C = 0	5.0		V
I_{CBO}	Collector-Cutoff Current	V_{CB} = 30 V		50	nA
I_{EBO}	Emitter-Cutoff Current	V_{EB} = 3.0 V, I_C = 0		50	nA
ON CHARACTERISTICS*					
h_{FE}	DC Current Gain	I_C = 0.1 mA, V_{CE} = 1.0 V I_C = 1.0 mA, V_{CE} = 1.0 V I_C = 10 mA, V_{CE} = 1.0 V I_C = 50 mA, V_{CE} = 1.0 V I_C = 100 mA, V_{CE} = 1.0 V	60 80 100 60 30	 300 	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 10 mA, I_B = 1.0 mA I_C = 50 mA, I_B = 5.0 mA		0.25 0.4	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 10 mA, I_B = 1.0 mA I_C = 50 mA, I_B = 5.0 mA	0.65	0.85 0.95	V V
SMALL SIGNAL CHARACTERISTICS					
f_T	Transition Frequency	I_C = 10 mA, V_{CE} = 20, f = 100 MHz	250		MHz
C_{cb}	Collector-Base Capacitance	V_{CB} = 5.0 V, I_E = 0, f = 100 kHz		4.5	pF
C_{eb}	Emitter-Base Capacitance	V_{EB} = 0.5 V, I_C = 0, f = 100 kHz		10	pF
h_{ie}	Input Impedance	V_{CE}= 10 V,I_C= 1.0 mA,f=1.0 kHz	2.0	12	kΩ
h_{fe}	Small-Signal Current Gain	V_{CE}= 10 V,I_C= 1.0 mA,f=1.0 kHz	100	400	
h_{oe}	Output Admittance	V_{CE}= 10 V,I_C= 1.0 mA,f=1.0 kHz	3.0	60	μS
SWITCHING CHARACTERISTICS					
t_d	Delay Time	I_C = 10 mA, I_{B1} = 1.0 mA,		35	ns
t_r	Rise Time	V_{EB} = 0.5 V		35	ns
t_s	Storage Time	I_C = 10 mA, I_{Bon} = I_{Boff} = 1.0 mA		275	ns
t_f	Fall Time			75	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 0.01%

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

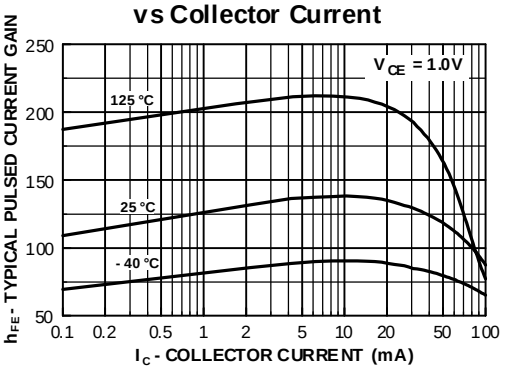
Spice Model

PNP (Is=1.41f Xti=3 Eg=1.11 Vaf=18.7 Bf=180.7 Ne=1.5 Ise=0 Ikf=80m Xtb=1.5 Br=4.977 Nc=2 Isc=0 Ikr=0 Rc=2.5 Cjc=9.728p Mjc=.5776 Vjc=.75 Fc=.5 Cje=8.063p Mje=.3677 Vje=.75 Tr=33.42n Tf=179.3p Itf=.4 Vtf=4 Xtf=6 Rb=10)

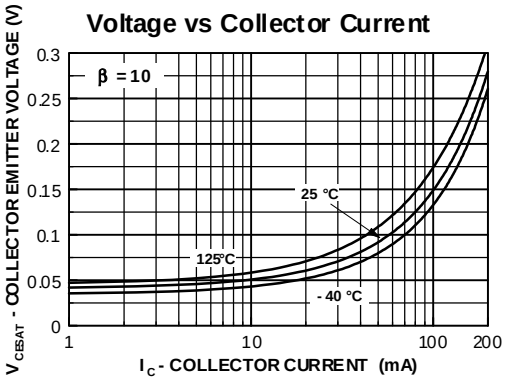
PNP General Purpose Amplifier
(continued)

Typical Characteristics

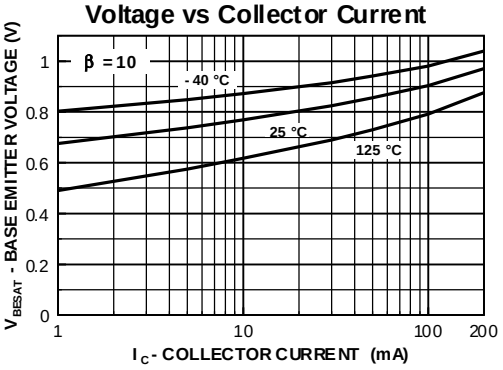
Typical Pulsed Current Gain vs Collector Current



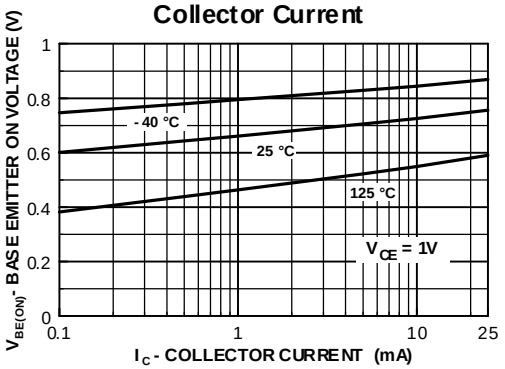
Collector-Emitter Saturation Voltage vs Collector Current



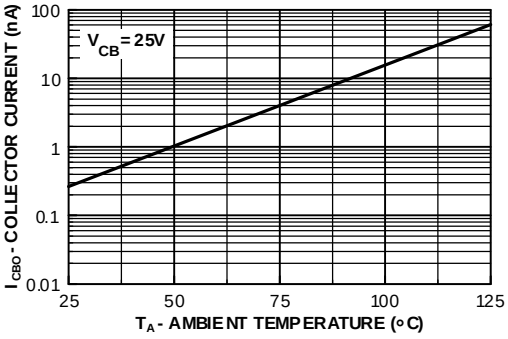
Base-Emitter Saturation Voltage vs Collector Current



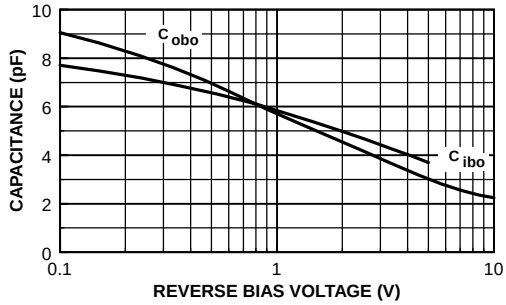
Base Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature

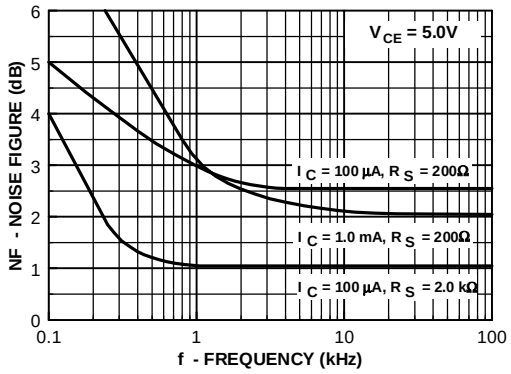


Common-Base Open Circuit Input and Output Capacitance vs Reverse Bias Voltage

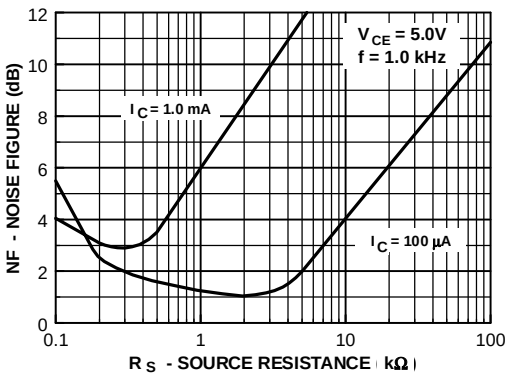


Typical Characteristics (continued)

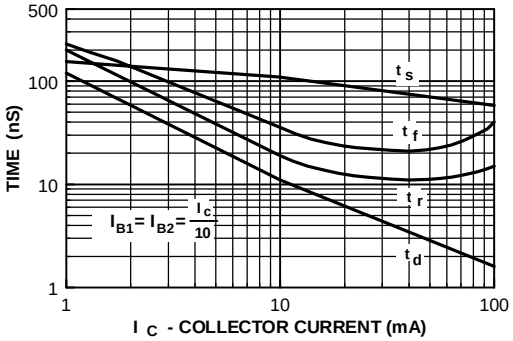
Noise Figure vs Frequency



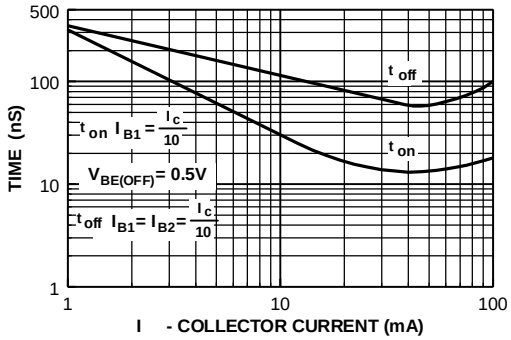
Noise Figure vs Source Resistance



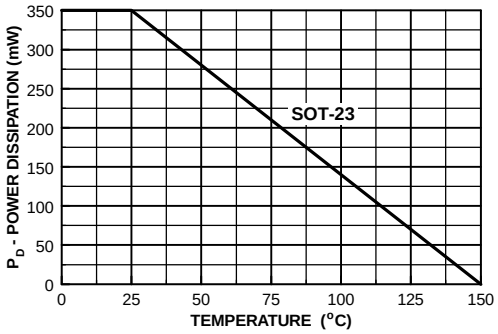
Switching Times vs Collector Current



Turn On and Turn Off Times vs Collector Current

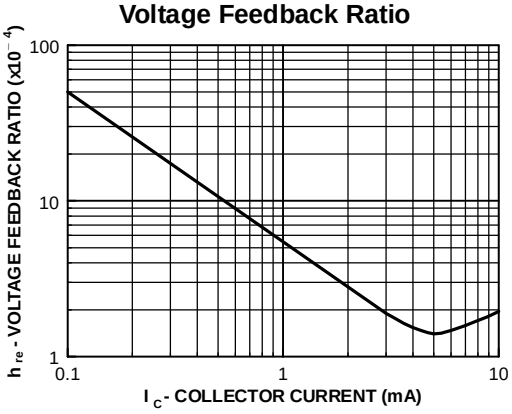


Power Dissipation vs Ambient Temperature

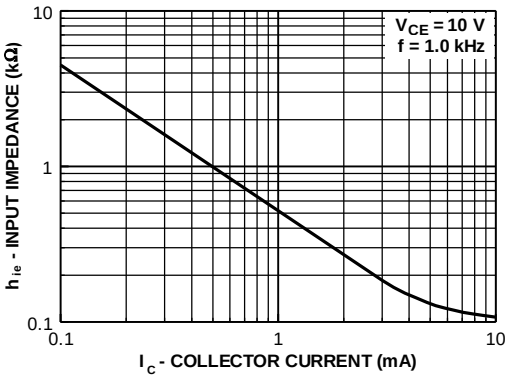


Typical Characteristics (continued)

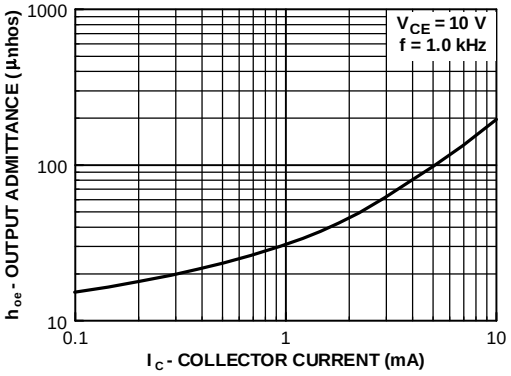
Voltage Feedback Ratio



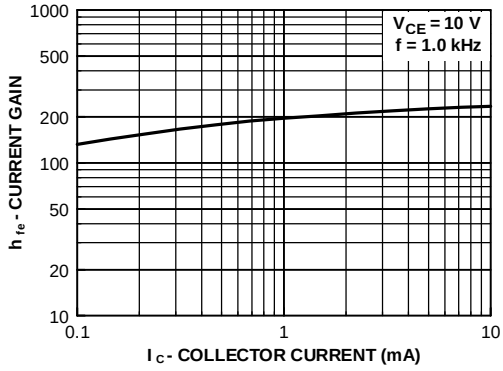
Input Impedance



Output Admittance



Current Gain



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